

HIGH SPEED 3.3V 2K X 8 DUAL-PORT STATIC RAM WITH

INTERRUPTS

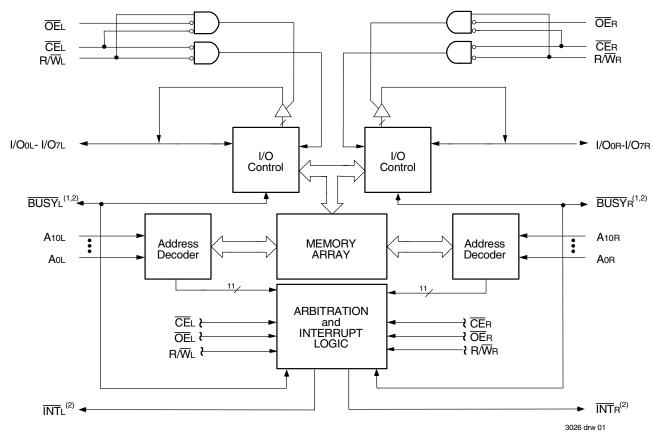
71V321L

Features

- High-speed access
 - Commercial & Industrial: 25/35ns (max.)
- Low-power operation
 - IDT71V321L Active: 325mW (typ.) Standby: 1mW (typ.)
- Two INT flags for port-to-port communications
- On-chip port arbitration logic (IDT71V321 only)
- BUSY output flag

- Fully asynchronous operation from either port
- Battery backup operation—2V data retention (L only)
- ◆ TTL-compatible, single 3.3V power supply
- Available in 52-pin PLCC, 64-pin TQFP and STQFP packages
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

Functional Block Diagram



NOTES:

- 1. IDT71V321 (MASTER): BUSY is an output
- 2. BUSY and INT are to tem-pole outputs.

JULY 2019

Description

The IDT71V321 is a high-speed 2K x 8 Dual-Port Static RAMs with internal interrupt logic for interprocessor communications. The IDT71V321 is designed to be used as a stand-alone 8-bit Dual-Port RAM.

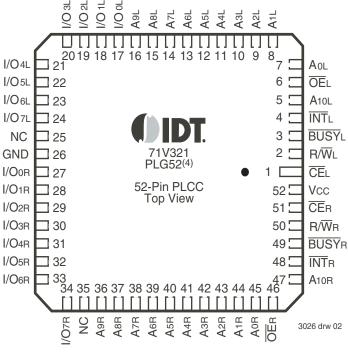
The device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by $\overline{\text{CE}}$, permits the on chip circuitry of each

port to enter a very low standby power mode.

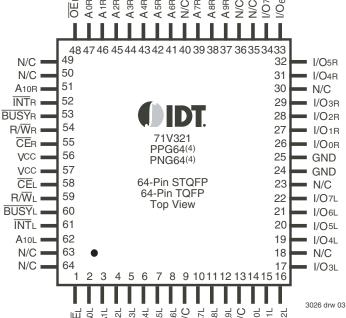
Fabricated using CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (L) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT71V321 devices are packaged in a 52-pin PLCC, a 64-pin TQFP (thin quad flatpack), and a 64-pin STQFP (super thin quad flatpack).

Pin Configurations (1,2,3)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply
- J52-1 package body is approximately .75 in x .75 in x .17 in. PP64-1 package body is approximately 10mm x 10mm x 1.4mm. PN64-1 package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.



Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Та	Operating Temperature	0 to +70	°C
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
ЮИТ	DC Output Current	50	mA

NOTES: 3026 tbl 01

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS
 may cause permanent damage to the device. This is a stress rating only
 and functional operation of the device at these or any other conditions
 above those indicated in the operational sections of the specification is not
 implied. Exposure to absolute maximum rating conditions for extended
 periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0MHz) TQFP Only$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF

NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Recommended Operating Temperature and Supply Voltage^(1,2)

Grade	Grade Ambient Temperature		Vcc		
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V		
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V		

3026 tbl 02

3026 tbl 03

NOTES:

- 1. This is the parameter Ta. This is the "instant on" case temperature.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	٧
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.0	_	VCC+0.3 ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V

- 1. V_{IL} (min.) = -1.5V for pulse width less than 20ns.
- 2. VTERM must not exceed Vcc + 0.3V.

DC Electrical Characteristics Over the Operating

Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

			71V321S		71V321L		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	Vcc = 3.6V, VIN = 0V to Vcc		10		5	μΑ
lLO	Output Leakage Current	$\overline{\text{CE}}$ = V _{IH} , V _{OUT} = 0V to V _{CC} V _{CC} = 3.6V		10		5	μΑ
Vol	Output Low Voltage	Iol = 4mA	_	0.4	_	0.4	V
Vон	Output High Voltage	Юн = -4mA	2.4	_	2.4	_	V

3026 tbl 04

NOTE:

1. At Vcc ≤ 2.0V input leakages are undefined.

3026 tbl 05

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(1,2)}$ (Vcc = 3.3V ± 0.3V)

						21X25 & Ind		21X35 & Ind		21X55 & Ind	
Symbol	Parameter	Test Condition	Versio	on	Тур.	Max.	Тур.	Max.	Тур.	Max.	Unit
lcc	Dynamic Operating Current	SEM = VIH f = fMAX ⁽³⁾	COM'L	S L	55 55	130 100	55 55	125 95	55 55	115 85	mA
	(Both Ports Active)	T = TMAX ⁽³⁾	IND	L	55	130	55	125	55	115	
ISB1	Standby Current (Both Ports - TTL	CER = CEL = VIH SEMR = SEML = VIH	COM'L	S L	15 15	35 20	15 15	35 20	15 15	35 20	mA
	Level Inputs)	$f = f_{MAX}^{(3)}$	IND	L	15	35	15	35	15	35	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{\text{CE}}$ "A" = V _{IL} and $\overline{\text{CE}}$ "B" = V _{IH} ⁽⁵⁾ Active Port Outputs Disabled, $f=\text{FMAX}^{(3)}$	COM'L	S L	25 25	75 55	25 25	70 50	25 25	60 40	mA
	Level inputs)	$\overline{SEMR} = \overline{SEML} = VIH$	IND	L	25	75	25	70	25	60	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports CE _L and CE _{R ≥} Vcc - 0.2V V _N > Vcc - 0.2V or	COM'L	S L	1.0 0.2	5 3	1.0 0.2	5 3	1.0 0.2	5 3	mA
	,	$\frac{V_{IN} \le 0.2V, f = 0^{(4)}}{SEMR} = \frac{SEML}{SEML} \ge VCC - 0.2V$	IND	L	0.2	6	1.0	5	1.0	5	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{\text{CE}}$ 'A' \leq 0.2V and $\overline{\text{CE}}$ 'B' \geq VCC - 0.2V ⁽⁵⁾ $\overline{\text{SEMR}}$ = $\overline{\text{SEML}}$ \geq VCC - 0.2V	COM'L	S L	25 25	70 55	25 25	65 50	25 25	55 40	mA
	TOWOS LEVEL IIIPUIS)	SEINIR = SEINIL \geq VCC - 0.2V VIN \geq VCC - 0.2V or VIN \leq 0.2V Active Port Outputs Disabled $f = f_{MAX}(^3)$	IND	L	25	70	25	65	25	55	

3026 tbl 06

NOTES:

- 1. 'X' in part numbers indicates power rating (S or L).
- 2. Vcc = 3.3V, TA = +25°C, and are not production tested. Icccc = 70mA (Typ.).
- 3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc and using "AC Test Conditions" of input levels of GND to 3V.
- 4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 5. Port "A" may be either left or right port. Port "B" is opposite from port "A".

Data Retention Characteristics (L Version Only)

Symbol	Parameter	Test Condition		Min.	Typ. ⁽¹⁾	Max.	Unit
VDR	Vcc for Data Retention			2.0	_	0	V
ICCDR	Data Retention Current	Vcc = 2v, CE ≥ Vcc - 0.2V	COM'L.	_	100	500	μΑ
tcdr ⁽³⁾	Chip Deselect to Data	VIN > VCC - 0.2V or VIN < 0.2V	IND.	_	100	1000	μΑ
	Retention Time			0	-	1	V
tR ⁽³⁾	Operation Recovery Time			trc ⁽²⁾	_	_	V

3026 tbl 07

- 1. Vcc = 2V, TA = +25°C, and is not production tested.
- 2. trc = Read Cycle Time.
- 3. This parameter is guaranteed by device characterization but not production tested.

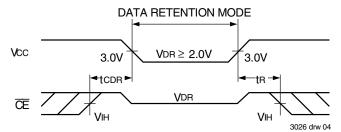


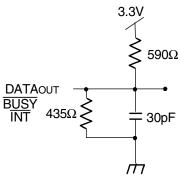
Industrial and Commercial Temperature Ranges

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

Data Retention Waveform





3026 tbl 08

Figure 1. AC Output Test Load

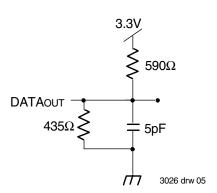


Figure 2. Output Test Load (for thz, tLz, twz, and tow)
* Including scope and jig.

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽²⁾

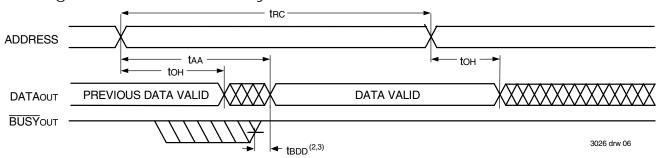
		71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
READ CYCLE									
trc	Read Cycle Time	25		35	_	55	_	ns	
taa	Address Access Time		25		35	_	55	ns	
tace	Chip Enable Access Time		25	_	35		55	ns	
taoe	Output Enable Access Time		12		20	_	25	ns	
tон	Output Hold from Address Change	3	_	3	_	3		ns	
tLZ	Output Low-Z Time ^(1,2)	0	_	0	_	0		ns	
tHZ	Output High-Z Time ^(1,2)		12		15	_	30	ns	
tpu	Chip Enable to Power Up Time ⁽²⁾	0		0		0		ns	
tpD	Chip Disable to Power Down Time ⁽²⁾		50		50	_	50	ns	

NOTES:

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. 'X' in part numbers indicates power rating (S or L).

3026 tbl 09

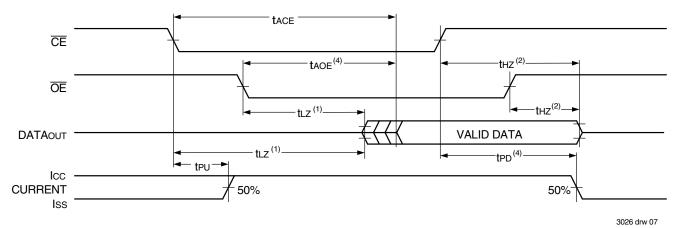
Timing Waveform of Read Cycle No. 1, Either Side(1)



NOTES:

- 1. $R/\overline{W} = V_{IH}$, $\overline{CE} = V_{IL}$, and is $\overline{OE} = V_{IL}$. Address is valid prior to the coincidental with \overline{CE} transition LOW.
- 2. tbdd delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

Timing Waveform of Read Cycle No. 2, Either Side (3)



- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is de-asserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. $R/\overline{W} = VIH$ and the address is valid prior to or coincidental with \overline{CE} transition LOW.
- 4. Start of valid data depends on which timing becomes effective last tage, tage, tage, tag, and tbdd.



AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁴⁾

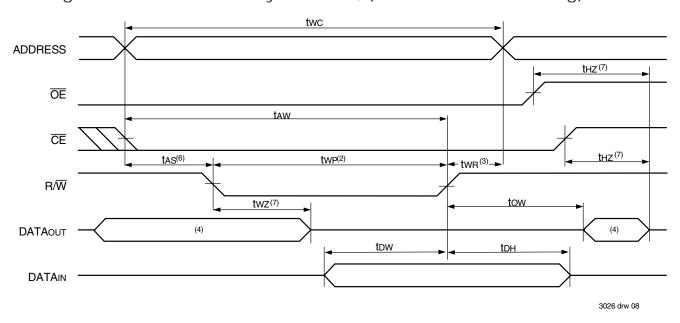
		71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind				
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit		
WRITE CYCLE										
twc	Write Cycle Time	25		35		55		ns		
tew	Chip Enable to End-of-Write	20	_	30		40		ns		
taw	Address Valid to End-of-Write	20	_	30		40		ns		
tas	Address Set-up Time	0	_	0		0		ns		
twp	Write Pulse Width	20	_	30		40		ns		
twr	Write Recovery Time	0	_	0		0		ns		
tow	Data Valid to End-of-Write	12	_	20		20		ns		
tHZ	Output High-Z Time ^(1,2)		12		15		30	ns		
tDH	Data Hold Time ⁽³⁾	0		0		0		ns		
twz	Write Enable to Output in High-Z ^(1,2)		15		15		30	ns		
tow	Output Active from End-of-Write ^(1,2)	0		0		0		ns		

NOTES: 3026 tbl 10

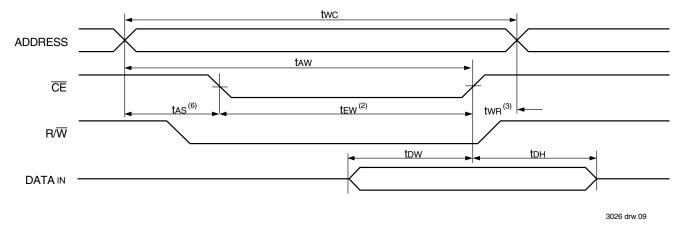
- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization but is not production tested.
- 3. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.
- $4. \quad \hbox{'X' in part numbers indicates power rating (S or L)}.$



Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)(1,5,8)



Timing Waveform of Write Cycle No. 2, (CE Controlled Timing)(1,5)



- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of $\overline{CE} = V_{IL}$ and R/W= V_{IL}.
- 3. twn is measured from the earlier of $\overline{\text{CE}}$ or R/\overline{W} going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined to be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during a R \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a R \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.



AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

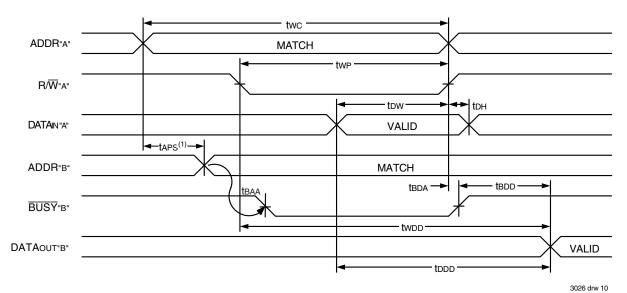
-		71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
BUSY Timing									
tbaa	BUSY Access Time from Address		20		20		30	ns	
tbda	BUSY Disable Time from Address		20	İ	20		30	ns	
TBAC	BUSY Access Time from Chip Enable	_	20		20	_	30	ns	
tBDC	BUSY Disable Time from Chip Enable		20		20		30	ns	
twн	Write Hold After BUSY ⁽⁵⁾	12		15	_	20		ns	
twdd	Write Pulse to Data Delay ⁽¹⁾	_	50		60		80	ns	
todo	Write Data Valid to Read Data Delay ⁽¹⁾	_	35	-	45	_	65	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5	_	5		ns	
tBDD	BUSY Disable to Valid Data ⁽³⁾	_	30	_	30	_	45	ns	

3026 tbl 11

NOTES:

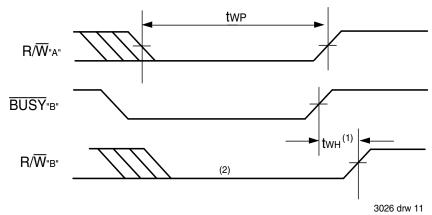
- 1. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY."
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 4. To ensure that a write cycle is inhibited on port "B" during contention on port "A".
- 5. To ensure that a write cycle is completed on port "B" after contention on port "A".
- 6. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Write with Port-to-Port Read and $\overline{\textbf{BUSY}}^{(2,3,4)}$



- 1. To ensure that the earlier of the two ports wins.
- 2 $\overline{CE}_L = \overline{CE}_R = V_{IL}$
- 3 OE=Vil.forthereadingport.
- 4 All timing is the same for the left and right ports. Port "A" may be either the left an right port. Port "B" is apposite from port "A".

Timing Waveform of Write with **BUSY**(3)



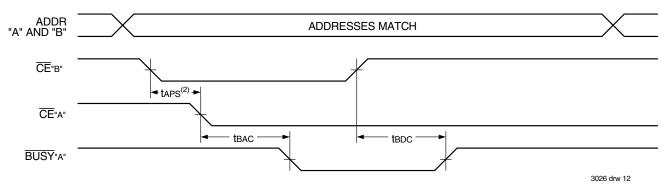
NOTES:

1. twn must be met for BUSY output 71V321.

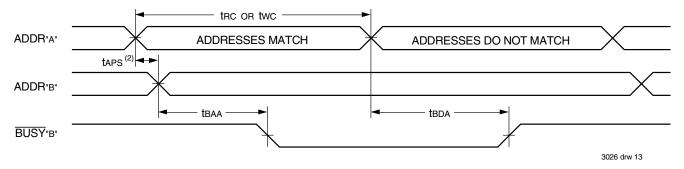
RENESAS

- 2. BUSY is asserted on port 'B' blocking R/W'B', until BUSY'B' goes HIGH.
- 3. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾



Timing Waveform of **BUSY** Arbitration Controlled by Address Match Timing⁽¹⁾



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisfied, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.



AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

		71V321X25 Com'l & Ind			21X35 & Ind	71V32 Com'l			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
INTERRUPT TIMING									
tas	Address Set-up Time	0	_	0	_	0	_	ns	
twr	Write Recovery Time	0	_	0	_	0		ns	
tins	Interrupt Set Time	_	25	_	25	_	45	ns	
tinr	Interrupt Reset Time		25	_	25	_	45	ns	

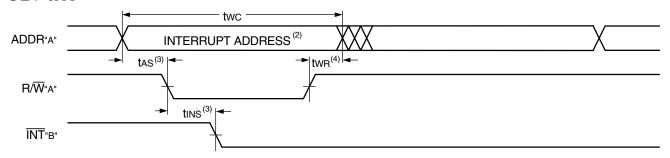
3026 tbl 12

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

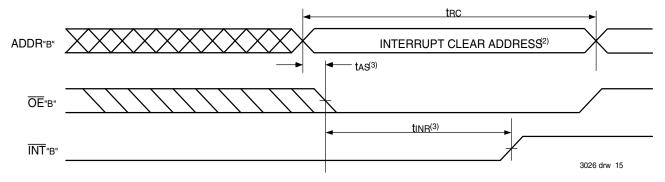
Timing Waveform of Interrupt Mode⁽¹⁾

SET **INT**



3026 drw 14

CLEAR **INT**



- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. See Interrupt Truth Table.
- 3. Timing depends on which enable signal ($\overline{\text{CE}}$ or R/ $\overline{\text{W}}$) is asserted last.
- 4. Timing depends on which enable signal (CE or R/W) is de-asserted first.

3026 tbl 14



71V321L High Speed 3.3V 2K x 8 Dual-Port Static RAM with Interrupts

Truth Tables

Table I — Non-Contention Read/Write Control⁽⁴⁾

Left or Right Port ⁽¹⁾					
R/W	CE	ŌĒ	D ₀₋₇	Function	
Х	Н	Х	X Port Deselected and in Power- Down Mode. ISB2 or ISB4		
Х	Н	Х	Z	$\overline{CER} = \overline{CEL} = VH$, Power-Down Mode IsB1 or ISB3	
L	L	Х	DATAIN	Data on Port Written Into Memory ⁽²⁾	
Н	L	L	DATAout	Data in Memory Output on Port ⁽³⁾	
Н	L	Н	Z	High-impedance Outputs	

·c.

NOTES:

- 1. $AOL A1OL \neq AOR A1OR$.
- 2. If $\overline{BUSY} = L$, data is not written.
- 3. If \overline{BUSY} = L, data may not be valid, see two and too timing.
- 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = High-impedance.

Table II — Interrupt Flag^(1,4)

				3						
Left Port				Right Port						
R/WL	CEL	ŌĒL	A10L-A0L	ĪÑT∟	R/W̄R	CER	OE R	A10R-A0R	Ī NT R	Function
L	L	Х	7FF	Х	Х	Х	Х	X	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	7FF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FE	Х	Set Left INTL Flag
Х	L	L	7FE	H ⁽²⁾	Χ	Х	Χ	Х	Χ	Reset Left INTL Flag

3026 thl 13

NOTES:

- 1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$
- 2. If $\overline{BUSY}L = VIL$, then No Change.
- 3. If $\overline{BUSY}R = VIL$, then No Change.
- 4. 'H' = HIGH, 'L' = LOW, 'X' = DON'T CARE

Table III — Address **BUSY** Arbitration

	ln	puts	Out	puts		
<u>C</u> E∟	CE _R	AOL-A10L AOR-A10R	BUSY _L (1)	BUSY _R (1)	Function	
Х	Χ	NO MATCH	Н	Н	Normal	
Н	Χ	MATCH	Н	Н	Normal	
Х	Н	MATCH	Н	Н	Normal	
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾	

3026 tbl 15

- Pins BUSYL and BUSYR are both outputs. BUSYx outputs on the IDT71V321 are to tempole.
- L'if the inputs to the opposite port were stable prior to the address and enable inputs of this
 port. 'H'if the inputs to the opposite port became stable after the address and enable inputs
 of this port. If taps is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR
 outputs cannot be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Functional Description

The IDT7V1321 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT71V321 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected $(\overline{\text{CE}} = V_{\text{H}})$. When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{\text{INTL}}$) is asserted when the right port writes to memory location 7FE (HEX), where a write is defined as the $\overline{\text{CE}}_R = R/\overline{W}_R = V_{\text{IL}}$ per Truth Table II. The left port clears the interrupt by accessing address location 7FE when $\overline{\text{CE}}_L = \overline{\text{OE}}_L = V_{\text{IL}}$, R/W is a "don't care". Likewise, the right port interrupt flag ($\overline{\text{INTR}}$) is asserted when the left port writes to memory location 7FF (HEX) and to clear the interrupt flag ($\overline{\text{INTR}}$), the right port must access the memory location 7FF. The message (8 bits) at 7FE or 7FF is user-defined, since it is an addressable SRAMlocation. If the interrupt function is not used, address locations 7FE and 7FF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table II for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation.

Depth Expansion

The BUSY arbitration, is based on the chip enable and address signals only. It ignores whether an access is a read or write.

The BUSY outputs on the IDT71V321 are totem-pole type outputs and do not require pull-up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate

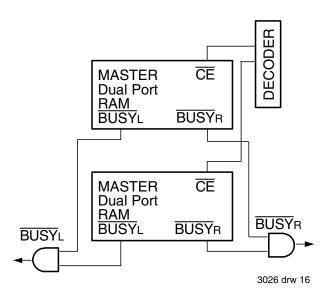
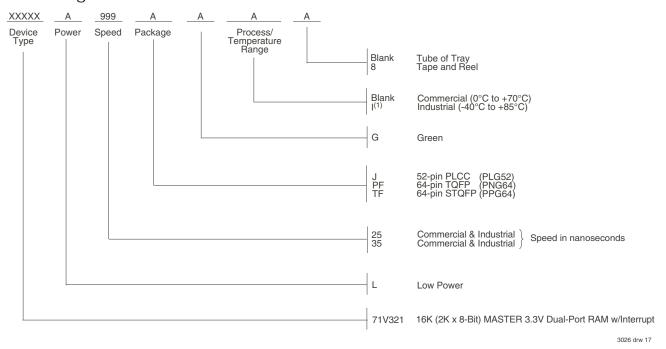


Figure 3. Busy and chip enable routing for depth expansion with IDT71V321.



Ordering Information



NOTES:

Contact your sales office Industrial temperature range is available for selected speeds, packages and powers.
 LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02
 Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
25	71V321L25JG	PLG52	LG52 PLCC	
	71V321L25JG8	PLG52	PLCC	С
	71V321L25PFG	PNG64	TQFP	С
	71V321L25PFG8	PNG64	TQFP	С
	71V321L25PFGI	PNG64	TQFP	I
	71V321L25PFGl8	PNG64	TQFP	I
	71V321L25TFG	PPG64	TQFP	С
	71V321L25TFG8	PPG64	TQFP	С
	71V321L25TFGI	PPG64	TQFP	I
35	71V321L35JG	PLG52	PLCC	С
	71V321L35JG8	PLG52	PLCC	С
	71V321L35JGI	PLG52	PLCC	I
	71V321L35JGl8	PLG52	PLCC	I
	71V321L35PFGI	PNG64	TQFP	I
	71V321L35PFGl8	PNG64	TQFP	I



Industrial and Commercial Temperature Ranges

Datasheet Document History

03/24/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections

Page 2 Added additional notes to pin configurations

06/15/99: Changed drawing format

10/15/99: Page 12 Changed open drain to totem-pole in Table III, note 1

10/21/99: Page 13 Deleted 'does not' in copy from Busy Logic

11/12/99: Replaced IDT logo

01/12/01: Page 1 & 2 Moved full "Description" to page 2 and adjusted page layouts

Page 3 Increased storage temperature parameters

Clarified TA parameter

Page 4 DC Electrical parameters—changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes

08/22/01: Page 4, 5, 7, 9 &11 Industrial temp range offering removed from DC & AC Electrical Chars for 35 and 55ns

01/17/06: Page 1 Added green availability to features

Page 14 Added green indicator to ordering information Page 1 & 14 Replaced old IDT™ with new IDT™ logo

08/25/06: Page 11 Changed INT"A" to INT"B" in the CLEAR INT drawing in the Timing Waveform of Interrupt Mode

10/23/08: Page 14 Removed "IDT" from orderable part number

01/25/10: Page 4 In order to correct the DC Chars table for the 71V321/71V421L35 speed grade and the Data Retention Chars

table, I Temp values have been added to each table respectively. In addition, all of the AC Chars tables and the

ordering information also now reflect this I temp correction

06/25/15: Page 2 Removed IDT in reference to fabrication

Page 2 & 14 The package codes J52-1, PN64-1 & PP64-1 changed to J52, PN64 & PP64 respectively to match standard

package codes

Page 14 Added Tape and Reel indicator to Ordering Information

10/14/15: Page 1-15 Removed 71V421S/L from the part number, in the pin configurations and throughout the datasheet

Page 1 - 15 Removed all references to Master/Slave throughout the datasheet

Page 1 -15 Updated the Com'l and Ind speeds for the 25/35/55ns offerings in Features, in the DC & AC Chars tables, in the

Ordering Information and throughout the datasheet

Page 13 Removed Width Expansion with Busy Logic Master/Slave Arrays diagram for part numbers 71V321/71V421S/L

and updated with a Depth Expansion diagram for the single part number 71V321S/L

Updated the corresponding Depth Expansion descriptive text in the Depth Expansion section of the datasheet

01/12/18: Product Discontinuation Notice - PDN# SP-17-02

Last time buy expires June 15, 2018

07/23/19: Page 2 Updated package codes J52 to PLG52, PP64 to PPG64 and PN64 to PNG64

Page 14 Added Orderable Part Information table

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